IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A semiconductor device having a portion thereof formed from a wafer of semiconductive material by a laser etching process comprising:

~~a substrate of semiconductive wafer material having a surface;~~

a semiconductor device having a plurality of bond pads located in the center of a surface thereof ~~portion thereof attached to a portion of the substrate~~; and

an interposer comprising silicon oxide coated silicon having the same size as the semiconductor device and a centrally located aperture therein having a portion of a surface thereof connected to the semiconductor device having the plurality of bond pads of the semiconductor device located in the aperture of the interposer to allow the connection of bond wires to the bond pads of the semiconductor device and to circuits of another surface of the interposer ~~substrate~~, the interposer having a laser roughened surface using a first laser at a first location increasing the surface area of a surface of the interposer to adhere mold material thereto in a molding operation, the surface roughened prior to the semiconductor device being attached to the interposer, the aperture in the interposer filled with mold material after the connection of bond wires between the bond pads of the semiconductor device and the circuits of the interposer ;

~~and~~

~~a portion of resist, contamination, and oxidation located on a portion of the surface of the substrate of semiconductive wafer material removed by laser etching of the resist, contamination, and oxidation from the surface of the substrate of semiconductive wafer material using a second laser forming a portion of an automolding system, the portion of resist, contamination, and oxidation removed by the second laser forming a portion of the automolding system prior to the encapsulation of a portion of the semiconductor device in the automolding system~~.

2. (Canceled)

3. (Previously Presented) The semiconductor device according to claim 1, wherein the laser includes one of an Nd:YAG laser and an excimer laser.

4. (Currently Amended) The semiconductor device according to claim 1, wherein the interposer ~~substrate~~ comprises a ball-grid-array interposer ~~substrate~~.

5. (Previously Presented) The semiconductor device according to claim 1, further comprising a vision system for detecting the resist.

6. (Previously Presented) The semiconductor device according to claim 5, wherein the vision system comprises:
a laser scanning system for detecting changes in a pattern of the substrate.

Claims 7 - 11 (Canceled)

12. (Withdrawn) A semiconductor device having a portion formed by a laser etching process on a substrate of semiconductive material having a surface comprising:
resist located on at least a portion of the surface having a portion thereof removed by etching the resist from the at least a portion of the surface of the substrate using a laser forming a roughened surface on the surface of the substrate of semiconductive material increasing the surface area of the surface to adhere mold material thereto .

13. (Withdrawn) The semiconductor device according to claim 12, wherein the laser comprises a laser associated with an automolding system.

14. (Withdrawn) The semiconductor device according to claim 12, wherein the laser includes one of an Nd:YAG laser and an excimer laser.

15. (Withdrawn) The semiconductor device according to claim 12, wherein the substrate comprises a ball-grid-array substrate.

16. (Withdrawn) The semiconductor device according to claim 12, further comprising a vision system for detecting the resist.

17. (Withdrawn) The semiconductor device according to claim 16, wherein the vision system comprises: a laser scanning system for detecting changes in a pattern of the substrate.

Claims 18 – 23 (Canceled)